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| APPLICATION NO. | FI | LING DATE | FIRST NAMED INVENTOR | ATTORNEY DOCKET NO. | CONFIRMATION NO |
|--------------------------------|-------|------------|----------------------|------------------------|-----------------|
| 09/342,235 | (| 06/29/1999 | YASUHIKO TAKEMURA | 0756-1980ELE | 6257 |
| 31780 | 7590 | 06/02/2005 | | EXAM | INER |
| ERIC ROB | INSON | | SEFER, AHMED N | | |
| PMB 955 21010 SOUTHBANK ST. | | | | ART UNIT | PAPER NUMBER |
| POTOMAC FALLS, VA 20165 | | | | 2826 | |
| | | | | DATE MAILED: 06/02/200 | 5 |

Please find below and/or attached an Office communication concerning this application or proceeding.

| | Application No. | Applicant(s) | | | | | |
|---|---|--|--|--|--|--|--|
| • | 09/342,235 | TAKEMURA, YASUHIKO | | | | | |
| Office Action Summary | Examiner | Art Unit | | | | | |
| | A. Sefer | 2826 | | | | | |
| The MAILING DATE of this communication a | | | | | | | |
| Period for Reply | | | | | | | |
| A SHORTENED STATUTORY PERIOD FOR REF THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a n - If INO period for reply is specified above, the maximum statutory perion - Failure to reply within the set or extended period for reply will, by state than three months after the mail earned patent term adjustment. See 37 CFR 1.704(b). | ال. 1.136(a). In no event, however, may a re eply within the statutory minimum of thirty od will عبدان and will expire SIX (0) MON ute, cause the application to become AB. | eply be timely filed y (30) days will be considered timely. THS from the malting date of this communication. ANDONED (35 U.S.C. § 133). | | | | | |
| Status | | | | | | | |
| 1)⊠ Responsive to communication(s) filed on 14 | March 2005. | | | | | | |
| | nis action is non-final. | | | | | | |
| · | | | | | | | |
| closed in accordance with the practice under | closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213. | | | | | | |
| Disposition of Claims | | | | | | | |
| 4)⊠ Claim(s) <u>6-11 and 13-25</u> is/are pending in th | e application | | | | | | |
| | 4a) Of the above claim(s) is/are withdrawn from consideration. | | | | | | |
| 5)⊠ Claim(s) <u>6-11</u> is/are allowed. | | | | | | | |
| 6)⊠ Claim(s) <u>13-25</u> is/are rejected. | | | | | | | |
| 7) Claim(s) is/are objected to. | | | | | | | |
| 8) Claim(s) are subject to restriction and | l/or election requirement. | | | | | | |
| Application Papers | | | | | | | |
| 9) The specification is objected to by the Exami | ner | | | | | | |
| 10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner. | | | | | | | |
| Applicant may not request that any objection to the | | | | | | | |
| Replacement drawing sheet(s) including the corre | ection is required if the drawing(| s) is objected to. See 37 CFR 1.121(d). | | | | | |
| 11) The oath or declaration is objected to by the | Examiner. Note the attached | Office Action or form PTO-152. | | | | | |
| Priority under 35 U.S.C. § 119 | | | | | | | |
| 12) Acknowledgment is made of a claim for foreign | an priority under 35 U.S.C. & | 119(a)-(d) or (f) | | | | | |
| a) All b) Some * c) None of: 1. Certified copies of the priority docume 2. Certified copies of the priority docume 3. Copies of the certified copies of the priority docume | ints have been received. Ints have been received in A | pplication No | | | | | |
| application from the International Bure | - | | | | | | |
| * See the attached detailed Office action for a li | , | received. | | | | | |
| | | | | | | | |
| Attachment(s) | _ | | | | | | |
| 1) Notice of References Cited (PTO-892) 2) D Notice of Draftsperson's Patent Drawing Review (PTO-948) | | ummary (PTO-413) s)/Mail Date | | | | | |
| 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/0 Paper No(s)/Mail Date 3/14/2005. | | nformal Patent Application (PTO-152) | | | | | |

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DETAILED ACTION

Response to Amendment

1. The amendment filed on March 14, 2005 has been entered; no new claims have been introduced.

Priority

2. Submission of the certified translation of the Japanese Priority Document (JP 3-296331) is acknowledged. Therefore, Yamazaki et al. USPN 6,331,723 is not available as a prior art.

Claim Rejections - 35 USC § 103

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 4. Claims 13-25 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yamazaki et al. ("Yamazaki") USPN 5,905,555 in view of Takahata ("Takahata") JP 63-76474.

Yamazaki discloses (see fig. 8 and col. 10, lines 36-40) a semiconductor device comprising a substrate 11 having an insulating surface; at least first and second semiconductor islands comprising polysilicon (as in claims 14, 17 and 21) formed over said substrate wherein each of the semiconductor islands has a channel region 28, 28' and a pair of impurity regions 34, 34'; a first and a second gate insulating film formed over said semiconductor island, respectively; at least first and second gate electrodes 40, 40' formed over said first and second semiconductor islands respectively with said first and second gate insulating films interposed therebetween; an interlayer insulating film 37 formed over a wiring (as in claims 16 and 19); a

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smoothing film 39 formed over a wiring (as in claims 20 and 23); a pixel electrode formed over said interlayer insulating film (as in claim 16) or a pixel electrode formed over said smoothing film (as in claim 20) and electrically connected to one of the pair of the impurity regions of the second semiconductor island; wherein the first semiconductor island is a part of an NTFT and the second semiconductor island is a part of a PTFT, but lacks anticipation of a wiring connecting one of the first impurity regions of the first semiconductor island with the second gate electrode.

Takahata discloses in figs. 2 and 6 a semiconductor device comprising a substrate 1 having an insulating surface; at least first and second semiconductor islands 2 comprising polysilicon (as in claims 14 and 17) formed directly on said insulating surface wherein each of the semiconductor islands has a channel region and a pair of impurity regions 5; a first and a second gate insulating film 3 formed over said semiconductor island, respectively; at least first and second gate electrodes 4 formed over said first and second semiconductor islands respectively with said first and second gate insulating films interposed therebetween; a wiring for electrically connecting one of the impurity regions of the first semiconductor island with the second gate electrode (fig. 2); an interlayer insulating film 3 formed over a wiring (as in claims 16 and 19); and wherein the first semiconductor island is a part of an NTFT and the second semiconductor island is a part of PTFT (abstract).

Therefore, in view of Takahata's teachings, one having an ordinary skill in the art at the time the invention was made would be motivated to modify Yamazaki's device by incorporating Takahata teachings since that would enhance speed as taught by Takahata.

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As to claims 15, 18 and 22, Yamazaki discloses a data line electrically connected to one impurity region of an NTFT.

As for claims 24 and 25, Takahata discloses in fig. 6 a voltage supply line 8 electrically connected to the other one of the pair of the impurity regions of the second semiconductor island.

Allowable Subject Matter

5. Claims 6-11 are allowed.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to A. Sefer whose telephone number is (571) 272-1921.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (571) 272-1915.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

ANS

May 22, 2005